IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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PATENT & TRADEMARK OFFICE

In re Applicant:		§	
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Arkadiy MORGENSHTEIN et al		§	
		§	
Serial No.: 10/825,123		§	
		§	
Filed:	April 16, 2004	§	Group Art Unit: 4128
		§	
For:	ION CONCENTRATION TRANSISTOR AND DUAL-MODE SENSORS (amended)	§	
		§	
		§	Attorney Docket: **27238**
Examiner:	John C. BALL	§	

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

DECLARATION UNDER 37 CFR 1.131

Sir:

I, Arkadiy MORGENSHTEIN of 11/51 Yigal Alon Street, Kiryat-Motzkin, Israel, declare as follows:

1. I am a joint inventor of the invention disclosed and claimed in the above-identified application;

2. I am the author of the Research Thesis titled "Design an Methodology of ISFET (Ion Sensitive Field Effect Transistor) Microsystems for Bio-Telemetry"; As stated on page 2 of the Thesis, the research was done under the supervision of Prof. Uri Dinnar and Prof. Yael Nemirovsky, who are named inventors in the above-identified application. The Research was submitted by me as my Reasearch Thesis, however, the work was jointly performed Profs. Dinnar, Nemirovsky and me. I am named as an author of the Thesis as is customary for Master students in their Research Thesis; and

3. The Research Thesis was presented by me on April 27, 2003, as is evidenced by a Transcript of Academic Record from the Technion – Israel Institute of Technology, attached and marked Annex A. The Research Thesis was not available to the public prior to that date.

I declare that all statements made herein of our knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements are made with the knowledge that willfully false statements are punishable by fine or imprisonment under 18 U.S.C. Section 1001 and that any such statement may jeopardize the validity of the subject application or any patent issued thereon.

Arkadiy MORGENSHTEIN

4.11.08.

Date: October , 2008